

**isc Silicon NPN Power Transistor**

**BUT11A**

**DESCRIPTION**

- High Voltage
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

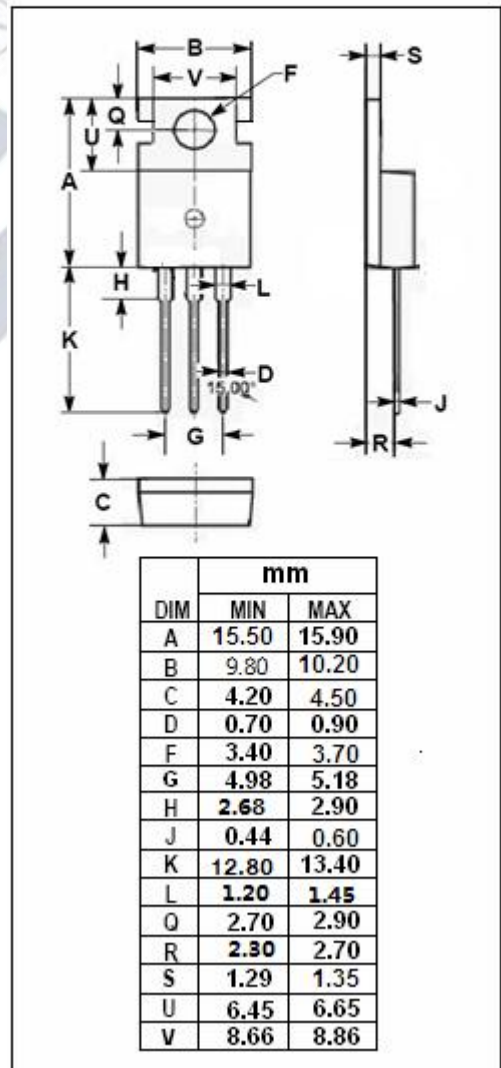
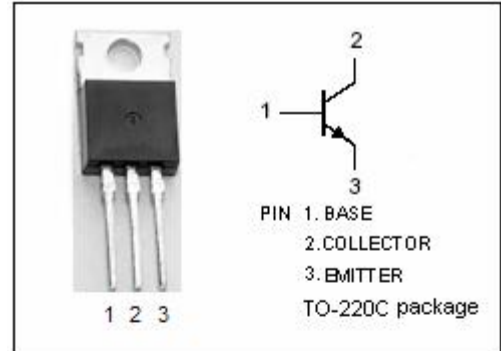
- Converters
- Inverters
- Switching regulators
- Motor control systems

**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1000	V
V <sub>CEO</sub>	Collector-Emitter Voltage	450	V
V <sub>EBO</sub>	Emitter-Base Voltage	9	V
I <sub>C</sub>	Collector Current-Continuous	5	A
I <sub>CM</sub>	Collector Current-Peak	10	A
I <sub>B</sub>	Base Current	2	A
P <sub>C</sub>	Collector Power Dissipation @T <sub>c</sub> =25°C	100	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.25	°C/W



**isc Silicon NPN Power Transistor****BUT11A****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE0(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=10\text{mA}; I_B=0$	450			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.33\text{A}$			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.33\text{A}$			1.3	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=\text{Rated } V_{CES}; V_{BE}=0$ $V_{CE}=\text{Rated } V_{CES}; V_{BE}=0; T_C=125^\circ\text{C}$			1 2	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=9\text{V}; I_C=0$			10	mA
$h_{FE-1}$	DC Current Gain	$I_C=5\text{mA}; V_{CE}=5\text{V}$	10		35	
$h_{FE-2}$	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	14		35	
$h_{FE-3}$	DC Current Gain	$I_C=2.5\text{A}; V_{CE}=5\text{V}$	9		17	

Switching Times; Resistive Load

$t_{on}$	Turn-on Time				1.0	$\mu\text{s}$
$t_s$	Storage Time	$I_C=2.5\text{A}; I_{B1}=-I_{B2}=0.5\text{A}$			4.0	$\mu\text{s}$
$t_f$	Fall Time				0.8	$\mu\text{s}$